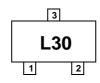


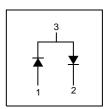
BAV23S **Small Signal Diode**







Connection Diagram



Absolute Maximum Ratings * Ta = 25°C unless otherwise noted

Symbol	Parameter	Value	Unit
V _{RRM}	Maximum Repetitive Reverse Voltage	250	V
I _{F(AV)}	Average Rectified Forward Current	200	mA
Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 microsecond Pulse Width = 100 microsecond		9.0 3.0	A A
T _{STG}	Storage Temperature Range	-55 to +150	°C
T _J Operating Junction Temperature		150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

Symbol	Parameter	Value	Unit
P_{D}	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient*	357	°C/W

Electrical Characteristics $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Max	Units
V_R	Breakdown Voltage	I _R = 100μA	250		V
V _F	Forward Voltage	I _F = 100mA I _F = 200mA		1.0 1.25	V V
I _R	Reverse Leakage	V _R = 250V V _R = 250V, T _A = 150°C		100 100	nA μA
t _{rr}	Reverse Recovery Time	$I_F = I_R = 30\text{mA}, I_{RR} = 3.0\text{mA},$ $R_L = 100\Omega$		50	ns

Typical Performance Characteristics

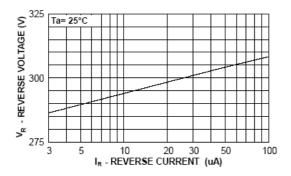
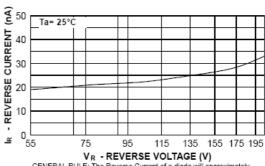


Figure 1. Reverse Voltage vs Reverse Current BV - 1.0 to $100 \mu A$



GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

Figure 2. Reverse Current vs Reverse Voltage IR - 55 to 205V

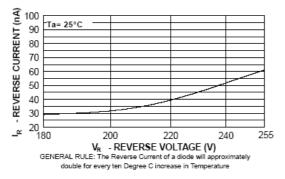


Figure 3. Reverse Current vs Reverse Voltage IR - 180 to 255V

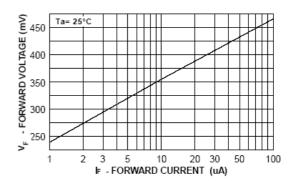


Figure 4. Forward Voltage vs Forward Current VF - 1.0 to 100μA

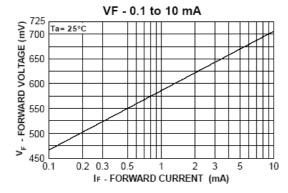


Figure 5. Forward Voltage vs Forward Current VF - 0.1 to 10mA

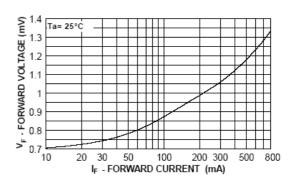


Figure 6. Forward Voltage vs Forward Current VF - 10 to 800mA

Typical Performance Characteristics (Continued)

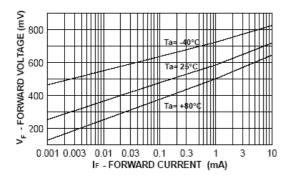


Figure 7. Forward Voltage vs Ambient Temperature VF - 1.0μA - 10mA (- 40 to +80°C)

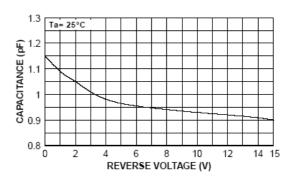


Figure 8. Capacitance vs Reverse Voltage VR - 0 to 5V

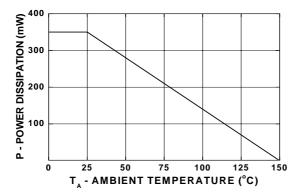


Figure 9. Power Derating Curve

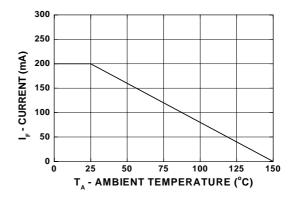


Figure 10. Average Rectified Current(I_O) vs Ambient Temperature(T_A)

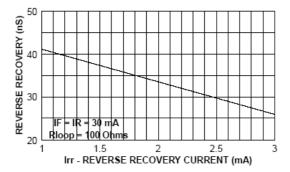
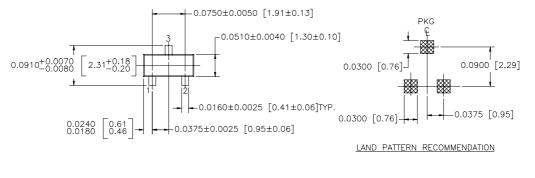
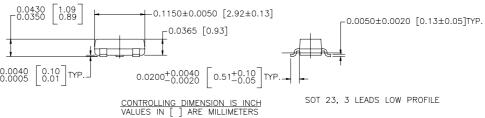


Figure 11. Reverse Recovery Time vs Reverse Recovery Current (Irr)

Mechanical Dimensions

SOT-23





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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